

isc Silicon NPN Power Transistors
TIP41C
DESCRIPTION

- DC Current Gain $-h_{FE} = 30(\text{Min})@ I_C = 0.3\text{A}$
- Collector-Emitter Sustaining Voltage-
: $V_{CEO(\text{SUS})} = 100\text{V}(\text{Min})$
- Complement to Type TIP42C
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

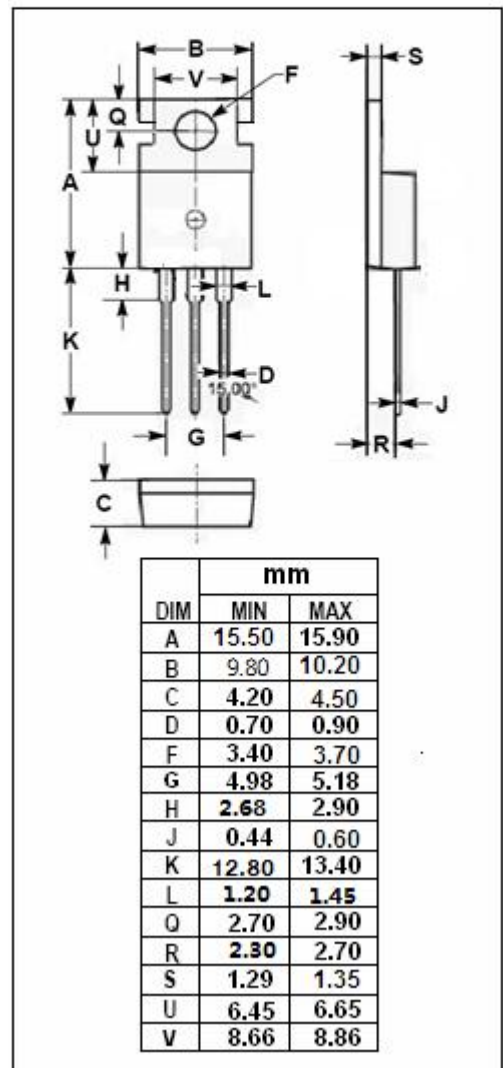
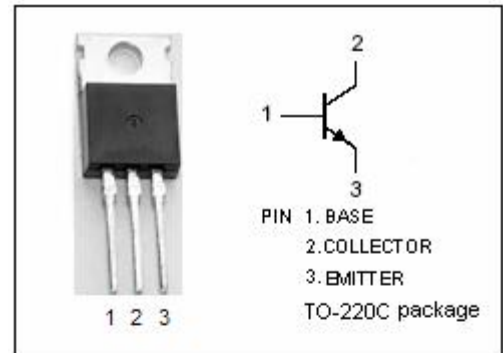
- Designed for use in general purpose amplifier and switching applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	100	V
V_{CEO}	Collector-Emitter Voltage	100	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	6	A
I_{CM}	Collector Current-Peak	10	A
I_B	Base Current	3	A
P_C	Collector Power Dissipation $T_C=25^\circ\text{C}$	65	W
	Collector Power Dissipation $T_a=25^\circ\text{C}$	2	
T_j	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-65~150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.92	$^\circ\text{C/W}$
$R_{th\ j-a}$	Thermal Resistance, Junction to Ambient	62.5	$^\circ\text{C/W}$



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ELECTRICAL CHARACTERISTICS $T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C= 30\text{mA}; I_B= 0$	100		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C= 6\text{A}; I_B= 1.5\text{A}$		1.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C= 6\text{A}; V_{CE}= 4\text{V}$		2.0	V
I_{CBO}	Collector Cutoff Current	$V_{CB}= 100\text{V}; I_E= 0$		0.4	mA
I_{CEO}	Collector Cutoff Current	$V_{CE}= 60\text{V}; I_B= 0$		0.7	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}= 5\text{V}; I_C= 0$		1.0	mA
h_{FE-1}	DC Current Gain	$I_C= 0.3\text{A}; V_{CE}= 4\text{V}$	30		
h_{FE-2}	DC Current Gain	$I_C= 3\text{A}; V_{CE}= 4\text{V}$	15		
f_T	Current-Gain—Bandwidth Product	$I_C= 0.5\text{A}; V_{CE}= 10\text{V}$	3		MHz

Switching Time

t_{on}	Turn-On Time	$I_C= 6\text{A}; I_{B1}= -I_{B2}= 0.6\text{A};$ $V_{BE(off)}= 4\text{V}, R_L= 5\ \Omega$		0.6	μs
t_{off}	Turn-Off Time			1.0	μs

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